# Quad 2-Input AND Gate with LSTTL Compatible Inputs

## **High-Performance Silicon-Gate CMOS**

The MC74HCT08A is identical in pinout to the LS08. The device inputs are compatible with Standard CMOS or LSTTL outputs.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 V to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 24 FETs or 6 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices

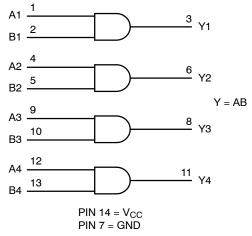


Figure 1. Logic Diagram

Pinout: 14-Lead Packages (Top View)

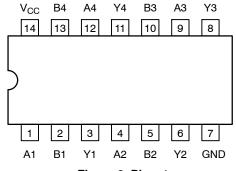


Figure 2. Pinout



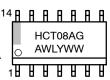
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#### MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A







= Assembly Location

WL, L = Wafer Lot

YY, Y = Year WW. W = Work Week

G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### **FUNCTION TABLE**

Inp	uts	Output
А В		Υ
L H H	H H	L L H

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> +0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>in</sub>	DC Input Current, per Pin	±20	mA
I <sub>out</sub>	DC Output Current, per Pin	±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±50	mA
P <sub>D</sub>	Power Dissipation in Still Air, SOIC Package <sup>†</sup> TSSOP Package <sup>†</sup>	500 450	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating - SOIC Package: - 7 mW/°C from 65°C to 125°C

TSSOP Package: – 6.1 mW/°C from 65°C to 125°C

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)		6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)		V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types		+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $ V_{CC} = 2.0 \text{ V} $ (Figure 3) $ V_{CC} = 4.5 \text{ V} $ $ V_{CC} = 6.0 \text{ V} $	0 0 0	1000 500 400	ns

#### DC CHARACTERISTICS (Voltages Referenced to GND)

			V <sub>CC</sub>	Guara	nteed Lim	nit	
Symbol	Parameter	Condition	v	-55 to 25°C	≤ <b>85</b> °C	≤125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out}$ = 0.1 V or $V_{CC}$ -0.1 V $ I_{out}  \le 20 \mu A$	4.5 to 5.5	2.0	2.0	2.0	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out}$ = 0.1 V or $V_{CC}$ - 0.1 V $\left I_{out}\right  \le 20 \mu A$	4.5 to 5.5	0.8	0.8	0.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$\begin{aligned} V_{in} &= V_{IH} \text{ or } V_{IL} \\  I_{out}  &\leq 20  \mu A \end{aligned}$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad  I_{out}  \le 4.0 \text{ mA}$	4.5	3.98	3.84	3.70	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad  I_{out}  \le 4.0 \text{ mA}$	4.5	0.26	0.33	0.40	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5	±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	1.0	10	40	μА

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### AC CHARACTERISTICS ( $C_L$ = 50 pF, Input $t_r$ = $t_f$ = 6 ns, $V_{CC}$ = 5.0 V $\pm$ 10%)

	V <sub>CC</sub>		Guaranteed Limit			
Symbol	Parameter	v	-55 to 25°C	≤ <b>85°C</b>	≤125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A or B to Output Y tplh (Figures 3 and 4) tphl	5.0	15 17	19 21	22 26	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 3 and 4)	5.0	15	19	22	ns
C <sub>in</sub>	Maximum Input Capacitance	•	10	10	10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V, V <sub>EE</sub> = 0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Buffer)*	20	pF

<sup>\*</sup>Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HCT08ADG	SOIC-14	55 Units / Rail
MC74HCT08ADR2G	(Pb-Free)	2500/Tape & Reel
MC74HCT08ADTR2G	TSSOP-14	2500/Topo & Book
NLV74HCT08ADTR2G*	(Pb-Free)	2500/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

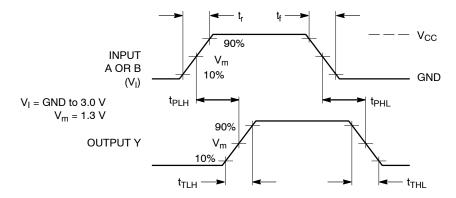
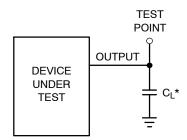


Figure 3. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 4. Test Circuit



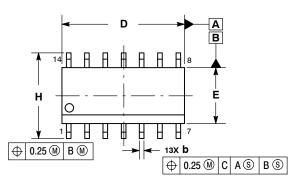
Figure 5. Expanded Logic Diagram (1/4 of the Device)

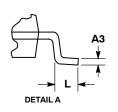


△ 0.10

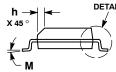
SOIC-14 NB CASE 751A-03 ISSUE L

**DATE 03 FEB 2016** 





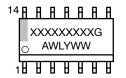




- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ASME Y14.5M, 1994.
    CONTROLLING DIMENSION: MILLIMETERS.
  - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIN	LLIMETERS INCHES		HES
DIM	MIN MAX		MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
Ĺ	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

#### **GENERIC MARKING DIAGRAM\***

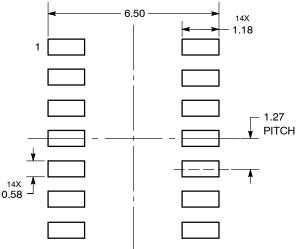


XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

# **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

C SEATING PLANE

#### **STYLES ON PAGE 2**

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

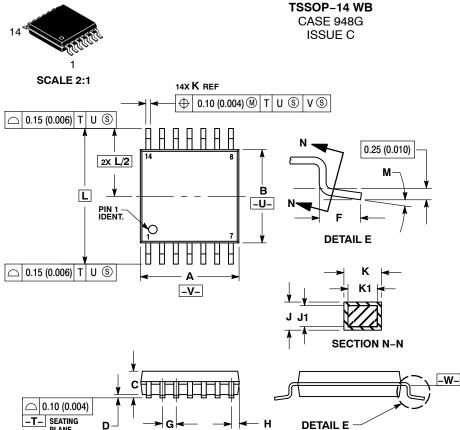
#### SOIC-14 CASE 751A-03 ISSUE L

### DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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**DATE 17 FEB 2016** 

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

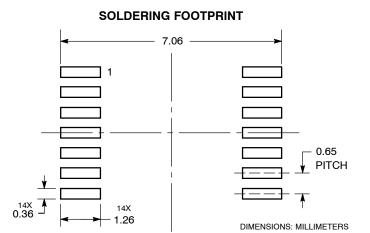
  3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE
  DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С	-	1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40		0.252	BSC
М	0°	8°	0°	8 °

#### **GENERIC MARKING DIAGRAM\***





= Assembly Location

= Wafer Lot = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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